Title: Qualification of RFAB as an additional Fab site option for select ABCD6 devices   Customer Contact: PCN Manager Dept: Quality Services   Proposed 1 <sup>st</sup> Ship Date: Jun 22, 2022 Estimated Sample Availability: Date provided at sample request.   Change Type: Clauge Type:   Assembly Site Assembly Process Assembly Materials   Design Electrical Specification Mechanical Specification   Test Site Packing/Shipping/Labeling Test Process   Wafer Bump Site Wafer Bump Material Wafer Bump Process   Wafer Fab Site Part number change Wafer Fab Process   PCN Details   Description of Change: Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab source for the selected devices listed in the "Product Affected" section.   Current Fab Site Additional Fab Site   Diameter Additional Fab Site Passivation Wafer Diameter									
Proposed 1 <sup>st</sup> Ship Date: Jun 22, 2022 Estimated Sample Availability: Date provided at sample request.   Change Type: Date Date Date Date Date   Assembly Site Assembly Process Assembly Materials   Design Electrical Specification Mechanical Specification   Test Site Packing/Shipping/Labeling Test Process   Wafer Bump Site Wafer Bump Material Wafer Bump Process   Wafer Fab Site Part number change Wafer Fab Process   Perconduction Perconduction of its RFAB fabrication facility as an additional Wafer Fab Site Additional Fab Site   Current Fab Site Passivation Mafer Diameter Additional Fab Site Passivation Wafer Diameter									
Proposed 1 <sup>st</sup> Ship Date: Jun 22, 2022 Estimated Sample Availability: Date provided at sample request.   Change Type: Assembly Site Assembly Process Assembly Materials   Design Electrical Specification Mechanical Specification   Test Site Packing/Shipping/Labeling Test Process   Wafer Bump Site Wafer Bump Material Wafer Bump Process   Wafer Fab Site Part number change Wafer Fab Process   PCN Details PCN Details   Description of Change: Current Fab Site Additional Fab Site   Current Fab Site Passivation Mafer Additional Fab Site Date Process Passivation   Mafer Fab Site Passivation Mafer Fab Site Additional Process Passivation Mafer Date Process Passivation									
Change Type: Availability: sample request.   Assembly Site Assembly Process Assembly Materials   Design Electrical Specification Mechanical Specification   Test Site Packing/Shipping/Labeling Test Process   Wafer Bump Site Wafer Bump Material Wafer Bump Process   Wafer Fab Site Wafer Fab Materials Wafer Fab Process   Part number change Part number change PCN Details   Description of Change: Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab source for the selected devices listed in the "Product Affected" section.   Current Fab Site Additional Fab Site   Current Fab Site Additional Fab Site   Diameter Fab Site									
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Design Electrical Specification Mechanical Specification   Test Site Packing/Shipping/Labeling Test Process   Wafer Bump Site Wafer Bump Material Wafer Bump Process   Wafer Fab Site Wafer Fab Materials Wafer Fab Process   Part number change Part number change Part number change   PCN Details   Description of Change:   Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab source for the selected devices listed in the "Product Affected" section.   Current Fab Site Additional Fab Site   Current Fab Site Additional Fab Site   Diameter Fab Site									
□ Test Site □ Packing/Shipping/Labeling □ Test Process   □ Wafer Bump Site □ Wafer Bump Material □ Wafer Bump Process   □ Wafer Fab Site □ Wafer Fab Materials □ Wafer Fab Process   □ Part number change □ Part number change □ Part number change   PCN Details   □ Part number change   □ Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab source for the selected devices listed in the "Product Affected" section.   Current Fab Site   □ Additional Fab Site   □ Process Passivation   Wafer Fab Site Additional Fab Site   □ Diamete									
Wafer Bump Site Wafer Bump Material Wafer Bump Process   Wafer Fab Site Wafer Fab Materials Wafer Fab Process   Part number change Part number change PCN Details   Description of Change: Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab source for the selected devices listed in the "Product Affected" section.   Current Fab Site Additional Fab Site   Current Process Passivation   Wafer Additional Fab Site Diameter									
Wafer Fab Site Wafer Fab Materials Wafer Fab Process   Part number change Part number change PCN Details   Description of Change: PCN Details PCN Details   Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab source for the selected devices listed in the "Product Affected" section. Additional Fab Site   Current Fab Site Additional Fab Site Passivation Wafer Fab Site   Current Fab Site Additional Process Passivation Wafer Diameter									
Part number change   PCN Details   Description of Change:   Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab source for the selected devices listed in the "Product Affected" section.   Current Fab Site Additional Fab Site   Current Fab Site Additional Fab Site   Description of Change: Description of its RFAB fabrication facility as an additional Wafer Fab Site   Current Fab Site Additional Fab Site   Diameter Fab Site Process Passivation Wafer Diameter									
PCN Details   PCN Details   Description of Change:   Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab source for the selected devices listed in the "Product Affected" section.   Current Fab Site   Additional Fab Site   Current Fab Site   Current Fab Site   Current Fab Site   Passivation Wafer   Fab Site Process Passivation Wafer   Diameter Fab Site Process Passivation Wafer									
Description of Change:   Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab source for the selected devices listed in the "Product Affected" section.   Current Fab Site   Additional Fab Site   Current Fab Site   Current Fab Site   Additional Fab Site   Current Fab Site   Passivation Wafer Diameter Additional Fab Site Passivation Wafer Diameter									
Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab source for the selected devices listed in the "Product Affected" section.   Current Fab Site   Additional Fab Site   Current Fab Site   Current Fab Site   Current Fab Site Additional Fab Site   Current Fab Site Additional Fab Site   Diameter Fab Site Process Passivation Wafer Diameter									
Current Fab SiteAdditional Fab SiteCurrent Fab SiteProcess PassivationPassivation DiameterWafer Fab SiteProcess PassivationWafer Diameter									
Current Fab SiteProcessPassivationWafer DiameterAdditional Fab SiteProcessPassivationWafer Diameter									
Current Fab SiteProcessPassivationWafer DiameterAdditional Fab SiteProcessPassivationWafer Diameter									
Fab Site   Diameter   Fab Site   Diameter									
ABCD6 SiN 200 mm RFAB ABCD6 SiON 300 mm									
Qual details are provided in the Qual Data Section.									
Reason for Change:									
Continuity of Supply									
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):									
None									
Changes to product identification resulting from this PCN:									
Current:									
Current Chip Site Chip Site Origin Code (20L) Chip Site Country Code (21L) Chip Site City									
MAINEFAB CUA USA South Portland									
New Fab Site:									
New Chip SiteChip Site Origin Code (20L)Chip Site Country Code (21L)Chip Site CityRFABRFBUSARichardson									
RFAD RFD USA RICIIAIUSUI									
Sample product shipping label (not actual product label)									
INSTRUMENTS G4 INC. (1P) SN74LS07NSR MADE IN: Malaysia (0) 2000 (D) 0226									
MSL 2 /260C/1 YEAR SEAL DT NALE: (31T)LOT: 3959047MLA MSL 1 /235C/UNLIM 03/29/04									
OPT: (P)									
TTEM: 39 (20) REV: (V) 0033317									
ITEM: 39 (2P) REV: (V) 0033917									
ITEM: 39 39 (2P) REV: (V) 0033917									

## Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

### Approved 02-Dec-2021

#### Qualification Results

### Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Mi n Lo t Qt y	SS/L ot	Test Name / Condition	Durati on	Qual Device: INA240A1QP WRQ1	Qual Device: INA240A2QP WRQ1	Qual Device: INA240A3QP WRQ1	Qual Device: <u>INA240A4QP</u> <u>WRQ1</u>	QBS Product Reference: <u>INA240A1QP</u> <u>WRQ1</u>	QBS Process Reference : <u>INA240A1E</u> <u>DQ1</u>	:	QBS Process Reference : <u>INA240A3E</u> <u>DQ1</u>
HAS T	A 2	A – Acce JEDE C JESD2 2- A110	lerate 3	d Envire	Diased Biased HAST, 130C/85%R H	96 Hours	1/77/0	-	-	-	3/231/0	1/77/0	1/77/0	1/77/0
UHA ST	A 3	JEDE C JESD2 2-a118	3	77	Unbiased HAST 130C/85%R H	96 Hours	1/79/0	-	-	-	3/231/0	1/77/0	1/77/0	1/77/0
тс	A 4	JEDE C JESD2 2- A104 and Appen dix 3	3	77	Temperatur e Cycle, - 65/150C	1000 Cycles	1/77/0	-	-	-	-	1/77/0	1/77/0	1/77/0
тс	A 4	JEDE C JESD2 2- A104 and Appen dix 3	3	77	Temperatur e Cycle, - 65/150C	1820 Cycles	-	-	-	-	-	1/77/0	1/77/0	1/77/0
Туре	#	Test Spec	Mi n Lo t Qt y	SS/L ot	Test Name / Condition	Durati on	Qual Device: I <u>NA240A1QP</u> <u>WRQ1</u>	Qual Device: INA240A2QP WRQ1	Qual Device: <u>INA240A3QP</u> <u>WRQ1</u>	Qual Device: <u>INA240A4QP</u> <u>WRQ1</u>	QBS Product Reference: <u>INA240A1QP</u> <u>WRQ1</u>	QBS Process Reference : <u>INA240A1E</u> <u>DQ1</u>	QBS Process Reference : <u>INA240A2E</u> <u>DQ1</u>	QBS Process Reference : INA240A3E DQ1
тс	A 4	JEDE C JESD2 2- A104 and Appen dix 3	3	77	Temperatur e Cycle, - 65/150C	2000 Cycles	-	-	-	-	-	1/77/0	1/73/0	1/73/0
тс	A 4	JEDE C JESD2 2- A104 and Appen dix 3	3	77	Temperatur e Cycle, - 65/150C	500 Cycles	1/77/0	-	-	-	3/242/1*	-	-	-
TC- WBP	A 4	MIL- STD88 3 Metho d 2011	1	60	Auto Post TC Bond Pull	30 ball bonds, min. 5 units	1/5/0	-	-	1/5/0	1/5/0	1/5/0	-	-
PTC	A 5	JEDE C JESD2 2-	1	45	Power Temperatur e Cycle	1000 Cycles	N/A	N/A	N/A	N/A	-	-	-	-
HTSL	A 6	A105 JEDE C JESD2 2- A103	1	45	High Temp Storage Bake 150C	1000 Hours	1/45/0		-	-	-	-	-	-
HTSL	A 6	JEDE C JESD2 2- A103	1	45	High Temp Storage Bake 175C	1000 Hours	-	-	-	-	-	1/45/0	-	-
HTSL	A 6	JEDE C JESD2 2- A103	1	45	High Temp Storage Bake 175C	500 Hours	-	-	-	-	1/45/0	-	-	-

	ype est G	#	Test Spec	Mi n Lo t Qt y	SS/L ot	Test Name / Condition me Simulation	Durati on Tests	Qual Device: <u>INA240A1QP</u> <u>WRQ1</u>	Qual Device: INA240A2QP WRQ1	Qual Device: <u>INA240A3QP</u> <u>WRQ1</u>	Qual Device: INA240A4QP WRQ1	QBS Product Reference: <u>INA240A1QP</u> <u>WRQ1</u>	QBS Process Reference : <u>INA240A1E</u> <u>DQ1</u>	QBS Process Reference : <u>INA240A2E</u> <u>DQ1</u>	QBS Process Reference : <u>INA240A3E</u> <u>DQ1</u>
$\square$	HTO L	B 1	JEDE C JESD2 2- A108	3	77	HTOL 150C	1000 Hours	-	-	-	-	-	1/77/0	1/77/0	1/77/0
ŀ	HTO L	B 1	JEDE C JESD2 2- A108	3	77	L/T 150C	408 Hours	1/77/0	-	-	-	2/222/0	-	-	-
ŀ	HTO L	В 1	JEDE C JESD2 2- A108	3	77	L/T 150C	500 Hours	-	-	-	-	1/77/0	-	-	-
E	LFR	В 2	ACE Q100- 008	3	800	Early Life Failure Rate 150C	48 Hours	-	-	-	-	-	1/800/0	1/800/0	1/800/0
E	EDR	B 3	AEC Q100- 005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	N/A	N/A	N/A	3/231/0 (oplife) 1/45/0 (data Retention)	-	-	
	Test		up C – Pa AEC	ckage	Assem	bly Integrity T Wire Bond	ests								
v	VBS	C 1	Q100- 001	1	30	Shear (Cpk>1.67)	-	1/30/0	-	-	-	1/30/0	-	-	-
v	VBP	C 2	MIL- STD88 3 Metho d 2011	1	30	Wire Bond Pull (Cpk>1.67)	-	1/30/0	-	-	-	1/30/0	-	-	-
	SD	С 3	JEDE C JESD2 2- B102	1	15	Surface Mount Solderability >95% Lead Coverage	Pb and Pb free	-	-	-	-	1/15/0 1/15/0	-	-	-
т	уре	#	Test Spec	Mi Lo t Qt y	SS/L ot	Test Name / Condition	Durati on	Qual Device: INA240A1QP WRQ1	Qual Device: <u>INA240A2QP</u> <u>WRQ1</u>	Qual Device: <u>INA240A3QP</u> <u>WRQ1</u>	Qual Device: <u>INA240A4QP</u> <u>WRQ1</u>	QBS Product Reference: <u>INA240A1QP</u> <u>WRQ1</u>	QBS Process Reference : <u>INA240A1E</u> <u>DQ1</u>	QBS Process Reference : <u>INA240A2E</u> <u>DQ1</u>	QBS Process Reference : INA240A3E DQ1
	PD	C 4	JEDE C JESD2 2- B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	-	-	-	-	-	3/30/0	-	-	-
	LI	C 6	JEDE C JESD2 2-	1	50	Lead Integrity	-	-	-	-	-	-	-	-	-
	Tes	t Gro	B105 up D – Di	e Fab	rication	Reliability Tes	ts								
	EM	D 1	JESD6 1	-	-	Electromigr ation	-	Completed Per Process Technology Requirement S	Completed Per Process Technology Requirement s	Completed Per Process Technology Requirement S	Completed Per Process Technology Requirement s	-	-	-	-
ſ	rdd B	D 2	JESD3 5	-	-	Time Dependent Dielectric Breakdown	-	Completed Per Process Technology Requirement S	Completed Per Process Technology Requirement S	Completed Per Process Technology Requirement S	Completed Per Process Technology Requirement S	-	-	-	
	нсі	D 3	JESD6 0 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirement S	Completed Per Process Technology Requirement S	Completed Per Process Technology Requirement S	Completed Per Process Technology Requirement S	-	-	-	
N	IBTI	D 4	-	-	-	Negative Bias Temperatur e Instability	-	Completed Per Process Technology Requirement S	Completed Per Process Technology Requirement S	Completed Per Process Technology Requirement S	Completed Per Process Technology Requirement S	-	-	-	-
	SM	D 5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirement s	Completed Per Process Technology Requirement s	Completed Per Process Technology Requirement S	Completed Per Process Technology Requirement s	-	-	-	-

	Test	Group E -	- Elec	trical V	erification Tes	ts								
нв	M E2	AEC Q100- 002	1	3	ESD - HBM - Q100	2500 V	1/3/0	-	-	-	-	1/3/0	1/3/0	1/3/0
НВ	M E2	AEC Q100- 002	1	3	ESD - HBM - Q100	3000 V	-	-	-	-	1/3/0	-	-	-
нв	M E2	AEC Q100- 002	1	3	ESD - HBM - Q100	4000 V	-	-	-	-	-	-	-	-
СD	M E3	AEC Q100- 011	1	3	ESD - CDM - Q100	1000 V	1/3/0	-	-	-	1/3/0	-	-	-
CD	M E3	AEC Q100- 011	1	3	ESD - CDM - Q100	1500 V	-	-	-	-	-	1/3/0	1/3/0	1/3/0
Lu	J E4	AEC Q100- 004	1	6	Latch-up	LU	1/6/0	-	-	-	1/6/0	1/6/0	1/6/0	1/6/0
E	) E5	AEC Q100- 009	3	30	Auto Electrical Distributions	Cpk>1.67 Room, hot, and cold test	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0

QBS: Qual By Similarity

- Qual Device INA240A3QPWRQ1 is gualified at LEVEL2-260C

Qual Device INA240A4QPWRQ1 is qualified at LEVEL2-260C

Qual Device INA240A2QPWRQ1 is qualified at LEVEL2-260C - Qual Device INA240A1QPWRQ1 is gualified at LEVEL2-260C

A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold: HTOL. ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

Green/Pb-free Status: Qualified Pb-Free (SMT) and Green

\*Mechanical Failure

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
WW PCN Team	PCN ww admin team@list.ti.com

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